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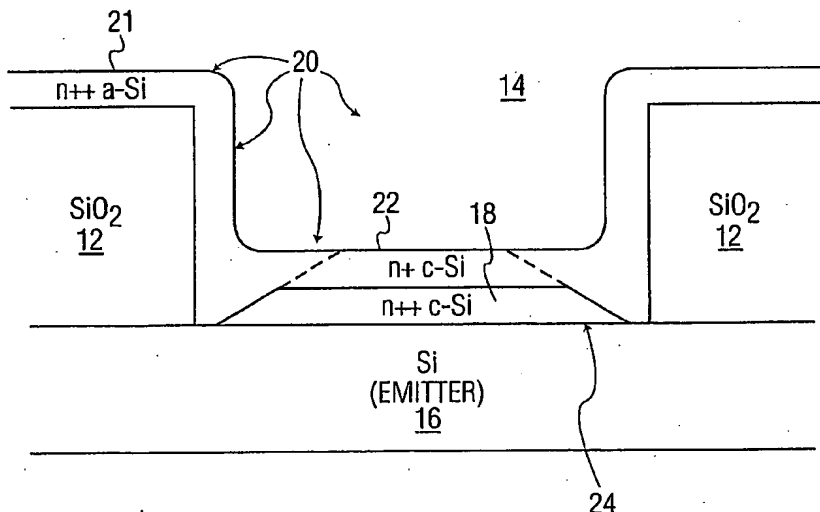
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(54) Title: **METHOD OF FABRICATING A MONO-CRYSTALLINE EMITTER**



(57) Abstract: Fabrication of a mono-crystalline emitter using a combination of selective and differential growth modes. The steps include providing a trench (14) formed on a silicon substrate (16) having opposed silicon oxide side walls (12); selectively growing a highly doped mono-crystalline layer (18) on the silicon substrate in the trench; and non-selectively growing a silicon layer (20) over the trench in order to form an amorphous polysilicon layer over the silicon oxide sidewalls.

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